March 1996



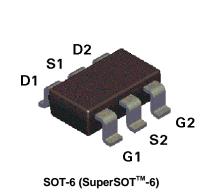
# NDC7002N Dual N-Channel Enhancement Mode Field Effect Transistor

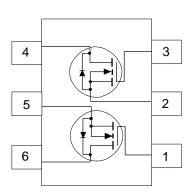
### **General Description**

These dual N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. These devices is particularly suited for low voltage applications requiring a low current high side switch.

## Features

- 0.51A, 50V,  $R_{DS(ON)} = 2\Omega @ V_{GS} = 10V$
- High density cell design for low R<sub>DS(ON)</sub>.
- Proprietary SuperSOT<sup>™</sup>-6 package design using copper lead frame for superior thermal and electrical capabilities.
- High saturation current.



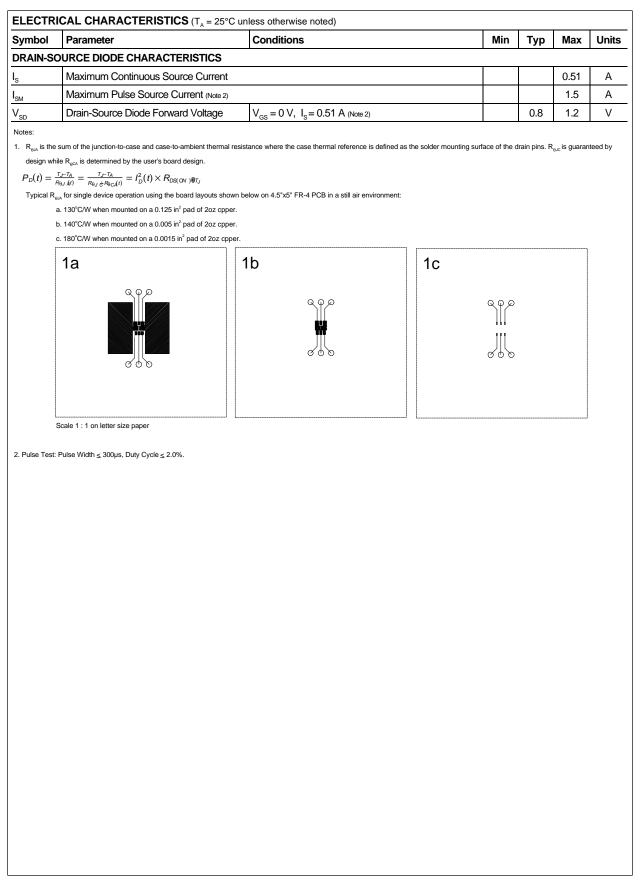


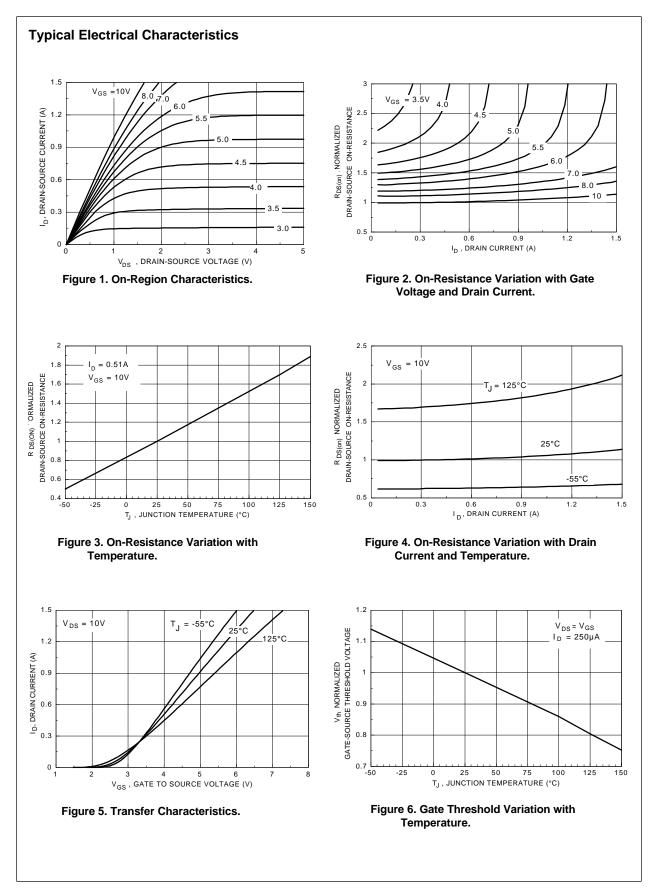
#### Absolute Maximum Ratings T<sub>4</sub> = 25°C unless otherwise noted

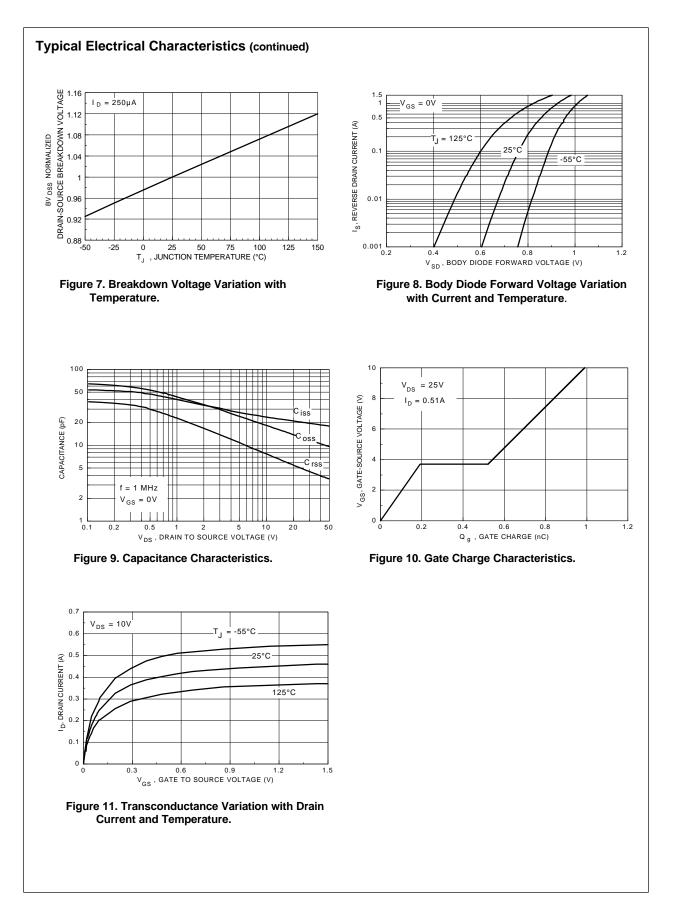
Symbol	Parameter		NDC7002N	Units
V <sub>DSS</sub>	Drain-Source Voltage		50	V
V <sub>GSS</sub>	Gate-Source Voltage - Continuous		20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	0.51	A
	- Pulsed		1.5	
P <sub>D</sub>	Maximum Power Dissipation	(Note 1a)	0.96	W
		(Note 1b)	0.9	
		(Note 1c)	0.7	
T <sub>J</sub> ,T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to 150	°C
THERMA	L CHARACTERISTICS			
R <sub>øja</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	130	°C/W
R <sub>øjc</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W

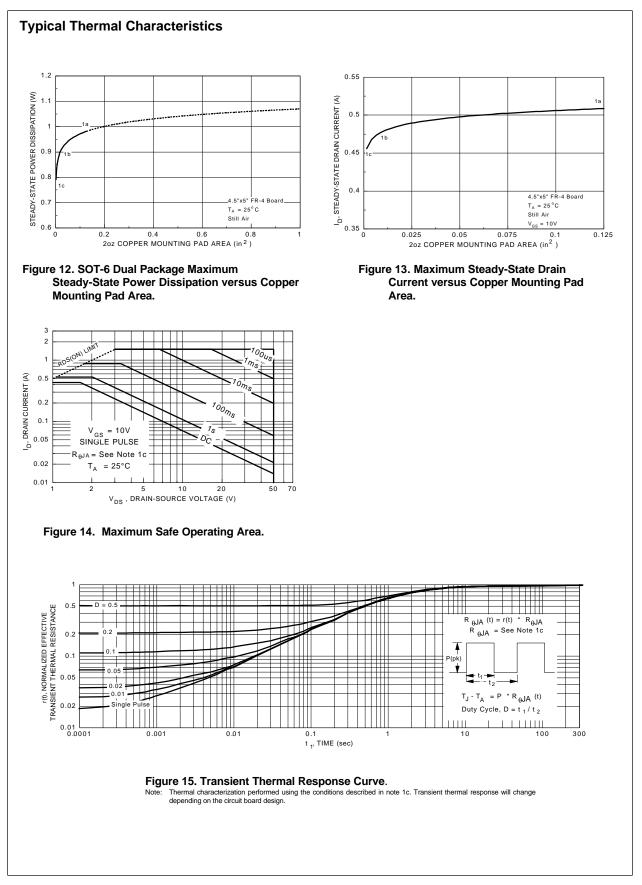
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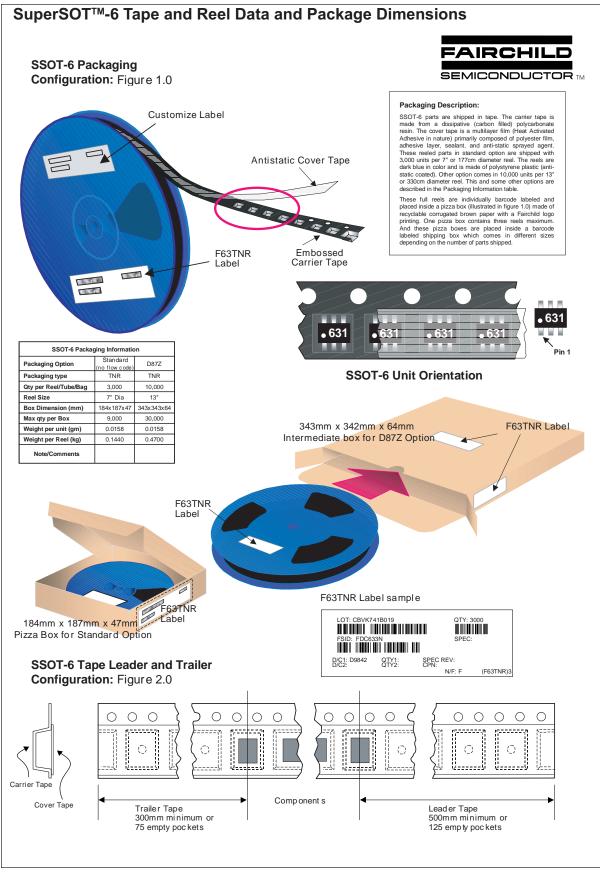
Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHA	ARACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		50			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$				1	μA
			T <sub>J</sub> = 125°C			500	
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I <sub>GSSR</sub>	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHAI	RACTERISTICS (Note 2)						
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{\rm DS}=V_{\rm GS},I_{\rm D}=250\;\mu A$		1	1.9	2.5	V
			T <sub>J</sub> = 125°C	0.8	1.5	2.2	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, \ I_{D} = 0.51 \text{ A}$			1	2	Ω
			T <sub>J</sub> = 125°C		1.7	3.5	
		$V_{GS} = 4.5 \text{ V}, \ I_{D} = 0.35 \text{ A}$			1.6	4	
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$		1.5			А
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.51 \text{ A}$			400		mS
DYNAMI	CHARACTERISTICS						<b>T</b>
C <sub>iss</sub>	Input Capacitance	$V_{\rm DS} = 25  \rm V, \ V_{\rm GS} = 0  \rm V,$			20		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz			13		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				5		pF
SWITCHI	NG CHARACTERISTICS (Note 2)						
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{_{DD}} = 25 \text{ V}, \ \text{I}_{_{D}} = 0.25 \text{ A},$			6	20	nS
t,	Turn - On Rise Time	$V_{\rm GS} = ~10~\rm V, R_{\rm GEN} = 25~\Omega$			6	20	
t <sub>D(off)</sub>	Turn - Off Delay Time	7			11	20	1
t <sub>r</sub>	Turn - Off Fall Time				5	20	1
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 25 V,			1		nC
Q <sub>gs</sub>	Gate-Source Charge	$I_{\rm D} = 0.51 \text{ Å}, V_{\rm GS} = 10 \text{ V}$			0.19		nC
Q <sub>gd</sub>	Gate-Drain Charge				0.33		nC



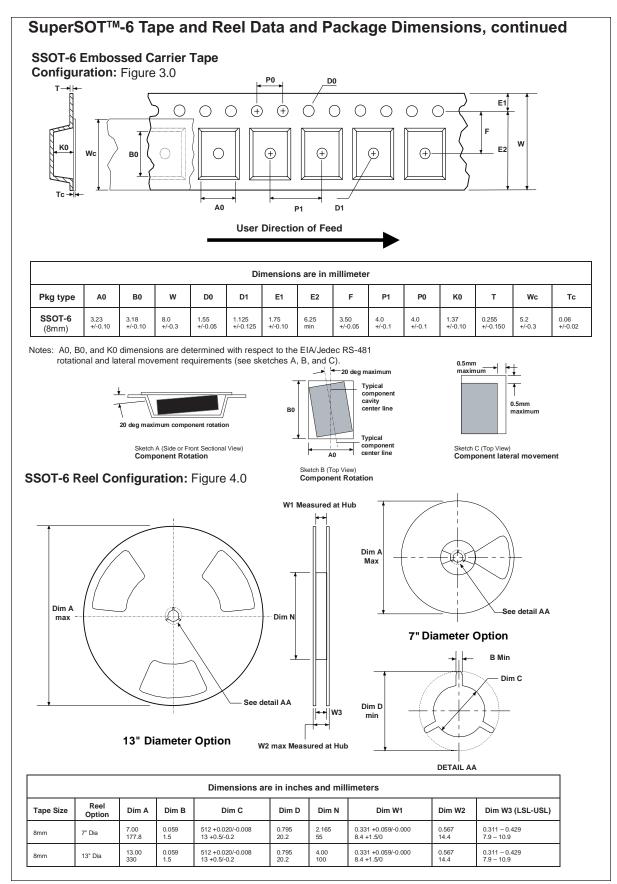




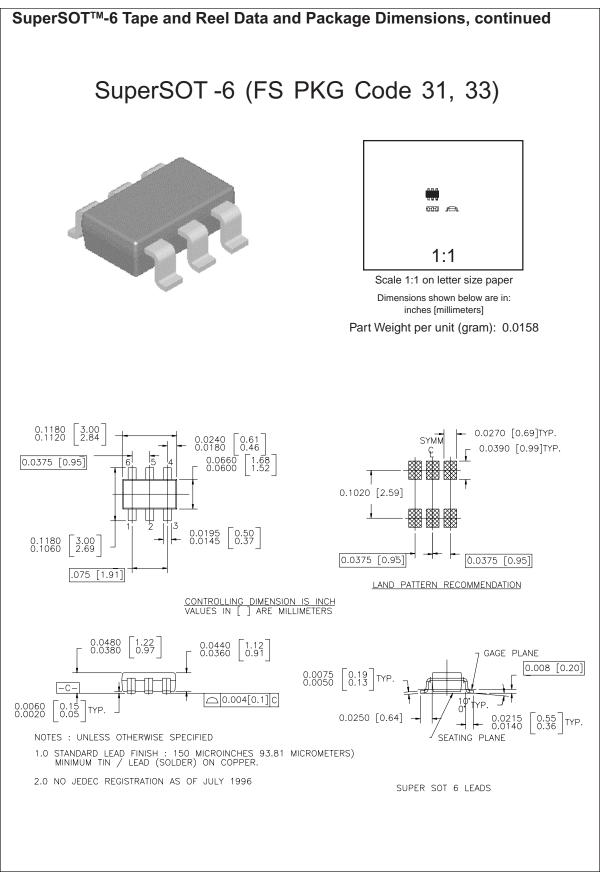




August 1999, Rev. C



July 1999, Rev. C



September 1998, Rev. A

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